## BSS138L, BVSS138L

## Power MOSFET <br> 200 mA, 50 V

## N-Channel SOT-23

Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

## Features

- Low Threshold Voltage ( $\mathrm{V}_{\mathrm{GS}(\mathrm{th})}$ : $\left.0.85 \mathrm{~V}-1.5 \mathrm{~V}\right)$ Makes it Ideal for Low Voltage Applications
- Miniature SOT-23 Surface Mount Package Saves Board Space
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Drain-to-Source Voltage | $\mathrm{V}_{\mathrm{DSS}}$ | 50 | Vdc |
| Gate-to-Source Voltage - Continuous | $\mathrm{V}_{\mathrm{GS}}$ | $\pm 20$ | Vdc |
| Drain Current <br> - Continuous @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> - Pulsed Drain Current $\left(\mathrm{t}_{\mathrm{p}} \leq 10 \mu \mathrm{~s}\right)$ | $\mathrm{I}_{\mathrm{D}}$ | 200 | mA |
| $\mathrm{I}_{\mathrm{DM}}$ | 800 |  |  |
| Total Power Dissipation @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 225 | mW |
| Operating and Storage Temperature <br> Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |
| Thermal Resistance, <br> Junction-to-Ambient | $\mathrm{R}_{\theta \mathrm{JA}}$ | 556 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Maximum Lead Temperature for <br> Soldering Purposes, for 10 seconds | $\mathrm{T}_{\mathrm{L}}$ | 260 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.


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$200 \mathrm{~mA}, 50 \mathrm{~V}$
$\mathrm{R}_{\mathrm{DS}(\text { on) }}=3.5 \Omega$

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| BSS138LT1G, <br> BVSS138LT1G | SOT-23 <br> (Pb-Free) | $3,000 /$ Tape \& Reel |
| BSS138LT7G | SOT-23 <br> (Pb-Free) | $3,500 /$ Tape \& Reel |
| BSS138LT3G, <br> BVSS138LT3G | SOT-23 <br> (Pb-Free) | $10,000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |

OFF CHARACTERISTICS

| Drain-to-Source Breakdown Voltage <br> $\left(V_{G S}=0\right.$ Vdc, $\left.I_{D}=250 \mu \mathrm{Adc}\right)$ | $\mathrm{V}_{(\mathrm{BR}) \mathrm{DSS}}$ | 50 | - | - | Vdc |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Zero Gate Voltage Drain Current |  |  |  |  |  |
| $\left(\mathrm{V}_{\mathrm{DS}}=25 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0 \mathrm{Vdc}, 25^{\circ} \mathrm{C}\right)$ |  |  |  |  | $\mu \mathrm{Adc}$ |
| $\left(\mathrm{V}_{\mathrm{DS}}=50 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0 \mathrm{Vdc}, 25^{\circ} \mathrm{C}\right)$ |  | - | - | 0.1 |  |
| $\left(\mathrm{~V}_{\mathrm{DS}}=50 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0 \mathrm{Vdc}, 150^{\circ} \mathrm{C}\right)$ |  | - | 0.5 |  |  |
| Gate-Source Leakage Current $\left(\mathrm{V}_{\mathrm{GS}}= \pm 20 \mathrm{Vdc}, \mathrm{V}_{\mathrm{DS}}=0 \mathrm{Vdc}\right)$ | - | 5.0 |  |  |  |

ON CHARACTERISTICS (Note 1)

| Gate-Source Threshold Voltage <br> $\left(V_{D S}=V_{G S}, I_{D}=1.0 \mathrm{mAdc}\right)$ | $\mathrm{V}_{\mathrm{GS}(\mathrm{th})}$ | 0.85 | - | 1.5 | Vdc |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Static Drain-to-Source On-Resistance <br> $\left(V_{G S}=2.75 \mathrm{Vdc}, \mathrm{I}_{\mathrm{D}}<200 \mathrm{mAdc}, \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}\right.$ to $\left.+85^{\circ} \mathrm{C}\right)$ <br> $\left(\mathrm{V}_{\mathrm{GS}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{D}}=200 \mathrm{mAdc}\right)$ | $\mathrm{r}_{\mathrm{DS}(\mathrm{on})}$ |  |  |  | $\Omega$ |
| Forward Transconductance <br> $\left(V_{\mathrm{DS}}=25 \mathrm{Vdc}, \mathrm{I}_{\mathrm{D}}=200 \mathrm{mAdc}, \mathrm{f}=1.0 \mathrm{kHz}\right)$ |  | - | 5.6 | 10 |  |

## DYNAMIC CHARACTERISTICS

| Input Capacitance | $\left(\mathrm{V}_{\mathrm{DS}}=25 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0, \mathrm{f}=1 \mathrm{MHz}\right)$ | $\mathrm{C}_{\text {iss }}$ | - | 40 | 50 | pF |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| Output Capacitance | $\left(\mathrm{V}_{\mathrm{DS}}=25 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0, \mathrm{f}=1 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{oss}}$ | - | 12 | 25 |  |
| Transfer Capacitance | $\left(\mathrm{V}_{\mathrm{DG}}=25 \mathrm{Vdc}, \mathrm{V}_{\mathrm{GS}}=0, \mathrm{f}=1 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{rss}}$ | - | 3.5 | 5.0 |  |

SWITCHING CHARACTERISTICS (Note 2)

| Turn-On Delay Time | $\left(\mathrm{V}_{\mathrm{DD}}=30 \mathrm{Vdc}, \mathrm{I}_{\mathrm{D}}=0.2 \mathrm{Adc},\right)^{\text {a }}$ | $\mathrm{t}_{\mathrm{d}(\mathrm{on})}$ | - | - | 20 | ns |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Turn-Off Delay Time |  | $\mathrm{t}_{\mathrm{d} \text { (off) }}$ | - | - | 20 |  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2 \%$.
2. Switching characteristics are independent of operating junction temperature.


Figure 1. On-Region Characteristics


Figure 3. On-Resistance Variation with Temperature


Figure 5. Gate Charge


Figure 2. Transfer Characteristics

Figure 4. Threshold Voltage Variation with Temperature


Figure 6. IDSS


Figure 7. On-Resistance versus Drain Current


Figure 9. On-Resistance versus Drain Current


Figure 11. Body Diode Forward Voltage


Figure 8. On-Resistance versus Drain Current


Figure 10. On-Resistance versus Drain Current


Figure 12. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS


Figure 13. Safe Operating Area


SOT-23 (TO-236)
CASE 318
ISSUE AT
DATE 01 MAR 2023

## SCALE 4:1


DETAIL


NDTES:

1. DIMENSIDNING AND TQLERANCING PER ASME Y14.5M,1994.
2. CDNTRDLLING DIMENSIDN: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF THE BASE MATERIAL.
4. DIMENSIUNS D AND E DO NDT INCLUDE MDLD FLASH, PRDTRUSIINS, DR GATE BURRS.

| DIM | MILLIMETERS |  | INCHES |  |  |  |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
|  | MIN. | NDM. | MAX. | MIN. | NDM. | MAX. |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| C | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| $H_{E}$ | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | $0^{\circ}$ | --- | $10^{\circ}$ | $0^{\circ}$ | --- | $10^{\circ}$ |



XXX = Specific Device Code
M = Date Code

- = Pb-Free Package
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Fr}$ dee indicator, " G " or microdot " P ", may or may not be present. Some products may not follow the Generic Marking.


RECDMMENDED M MUNTING FOUTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the QN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


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| :---: | :---: | :---: | :---: | :---: | :---: |
| STYLE 9: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. CATHODE | STYLE 10: <br> PIN 1. DRAIN <br> 2. SOURCE <br> 3. GATE | STYLE 11: <br> PIN 1. ANODE <br> 2. CATHODE <br> 3. CATHODE-ANODE | STYLE 12: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. ANODE | STYLE 13: <br> PIN 1. SOURCE <br> 2. DRAIN <br> 3. GATE | STYLE 14: <br> PIN 1. CATHODE <br> 2. GATE <br> 3. ANODE |
| STYLE 15: <br> PIN 1. GATE <br> 2. CATHODE <br> 3. ANODE | STYLE 16: <br> PIN 1. ANODE <br> 2. CATHODE <br> 3. CATHODE | STYLE 17: <br> PIN 1. NO CONNECTION <br> 2. ANODE <br> 3. CATHODE | STYLE 18: <br> PIN 1. NO CONNECTION <br> 2. CATHODE <br> 3. ANODE | STYLE 19: <br> PIN 1. CATHODE <br> 2. ANODE <br> 3. CATHODE-ANODE | STYLE 20 : <br> PIN 1. CATHODE <br> 2. ANODE <br> 3. GATE |
| STYLE 21: <br> PIN 1. GATE <br> 2. SOURCE <br> 3. DRAIN | STYLE 22: <br> PIN 1. RETURN <br> 2. OUTPUT <br> 3. INPUT | STYLE 23: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. CATHODE | STYLE 24: <br> PIN 1. GATE <br> 2. DRAIN <br> 3. SOURCE | STYLE 25: <br> PIN 1. ANODE <br> 2. CATHODE <br> 3. GATE | STYLE 26: <br> PIN 1. CATHODE <br> 2. ANODE <br> 3. NO CONNECTION |
| STYLE 27: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. CATHODE | STYLE 28: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. ANODE |  |  |  |  |


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